



#### 60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

### **Product Summary**

| BV <sub>DSS</sub> | Rds(on) Max                    | I <sub>D</sub> Max<br>Tc = +25°C |  |
|-------------------|--------------------------------|----------------------------------|--|
|                   | $2m\Omega$ @ $V_{GS} = 10V$    | 205A                             |  |
| 60V               | 3mΩ @ V <sub>GS</sub> = 6V     | 170A                             |  |
|                   | 3.3mΩ @ V <sub>GS</sub> = 4.5V | 165A                             |  |

#### **Features**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- Thermally Efficient Package Cooler Running Applications
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On-State Losses
- <1.1mm Package Profile Ideal for Thin Applications</li>
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <a href="https://www.diodes.com/quality/product-definitions/">https://www.diodes.com/quality/product-definitions/</a>

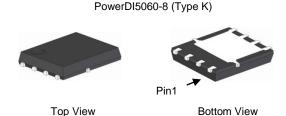
## **Description and Applications**

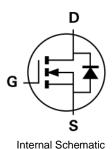
This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

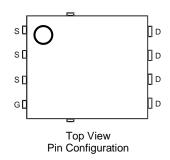
- Switching
- Synchronous Rectification
- DC-DC Converters

### **Mechanical Data**

- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208<sup>®</sup>
- Weight: 0.097 grams (Approximate)







#### **Ordering Information** (Note 4)

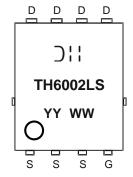
| - 7 |                |                        |                     |
|-----|----------------|------------------------|---------------------|
|     | Part Number    | Case                   | Packaging           |
|     | DMTH6002LPS-13 | PowerDI5060-8 (Type K) | 2,500 / Tape & Reel |

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- <1000ppm antimony compounds.

  4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



D:: = Manufacturer's Marking
TH6002LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 21 = 2021)
WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

| Characteristic  |                                   | Symbol          | Value      | Unit |
|---|-----------------------------------|-----------------|------------|------|
| Drain-Source Voltage  | VDSS                              | 60              | V          |      |
| Gate-Source Voltage   |                                   | $V_{GSS}$       | ±20        | V    |
| Continuous Drain Current, V <sub>GS</sub> = 10V (Note 6)        | $T_C = +25$ °C<br>$T_C = +100$ °C | ΙD              | 205<br>145 | Α    |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)              |                                   | I <sub>DM</sub> | 820        | Α    |
| Continuous Body Diode Forward Current (Note 6)                  | Tc = +25°C                        | Is              | 205        | Α    |
| Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%) | I <sub>SM</sub>                   | 820             | Α          |      |
| Avalanche Current, L = 3mH                                      | las                               | 14              | Α          |      |
| Avalanche Energy, L = 3mH                                       | E <sub>AS</sub>                   | 294             | mJ         |      |

### **Thermal Characteristics**

| Characteristic   |                | Symbol           | Value       | Unit |
|--|----------------|------------------|-------------|------|
| Total Power Dissipation (Note 5)                               | $T_A = +25$ °C | PD               | 3           | W    |
| Thermal Resistance, Junction to Ambient (Note 5)  Steady State |                | $R_{\theta JA}$  | 50          | °C/W |
| Total Power Dissipation (Note 6)                               | PD             | 167              | W           |      |
| Thermal Resistance, Junction to Case (Note 6)                  | Rejc           | 0.9              | °C/W        |      |
| Operating and Storage Temperature Range                        |                | $T_{J_i}T_{STG}$ | -55 to +175 | °C   |

### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

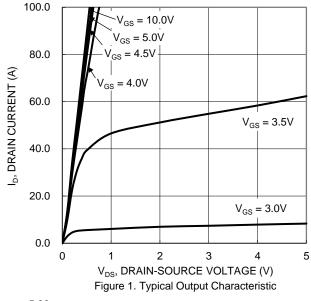
| Characteristic                             | Symbol              | Min | Тур   | Max  | Unit  | Test Condition   |  |
|--|---------------------|-----|-------|------|-------|--|--|
| OFF CHARACTERISTICS (Note 7)               |                     |     |       |      |       |  |  |
| Drain-Source Breakdown Voltage             | BV <sub>DSS</sub>   | 60  | _     | _    | V     | $V_{GS} = 0V, I_D = 250\mu A$                            |  |
| Zero Gate Voltage Drain Current            | IDSS                | 1   | _     | 1    | μΑ    | V <sub>DS</sub> = 48V, V <sub>GS</sub> = 0V              |  |
| Gate-Source Leakage                        | I <sub>GSS</sub>    |     | _     | ±100 | nA    | $V_{GS} = \pm 20V, V_{DS} = 0V$                          |  |
| ON CHARACTERISTICS (Note 7)                |                     |     |       |      |       |  |  |
| Gate Threshold Voltage                     | V <sub>GS(TH)</sub> | 1   | _     | 3    | V     | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$                     |  |
|  |                     |     | 1.7   | 2    |       | V <sub>G</sub> S = 10V, I <sub>D</sub> = 30A             |  |
| Static Drain-Source On-Resistance          | RDS(ON)             | _   | 2     | 3    | mΩ    | Vgs = 6V, ID = 30A                                       |  |
|  |                     | _   | 2.3   | 3.3  |       | $V_{GS} = 4.5V, I_D = 30A$                               |  |
| Diode Forward Voltage                      | VsD                 | _   | _     | 1.2  | V     | Vgs = 0V, Is = 50A                                       |  |
| DYNAMIC CHARACTERISTICS (Note 8)           |                     |     |       |      |       |  |  |
| Input Capacitance                          | Ciss                | _   | 6555  | _    |       | V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V,<br>f = 1MHz |  |
| Output Capacitance                         | Coss                | _   | 2264  | _    | pF    |  |  |
| Reverse Transfer Capacitance               | Crss                | _   | 187   | _    |       |  |  |
| Gate Resistance                            | Rg                  | _   | 0.7   | _    | Ω     | $V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$               |  |
| Total Gate Charge (V <sub>GS</sub> = 10V)  | $Q_g$               | _   | 130.8 | _    |       |  |  |
| Total Gate Charge (V <sub>GS</sub> = 4.5V) | Qg                  | _   | 63.6  | _    | nC    | V <sub>DS</sub> = 30V, I <sub>D</sub> = 50A              |  |
| Gate-Source Charge                         | Qgs                 | _   | 20.8  | _    | nc nc |  |  |
| Gate-Drain Charge                          | $Q_{gd}$            | _   | 29.4  | _    |       |  |  |
| Turn-On Delay Time                         | t <sub>D</sub> (ON) | _   | 11.2  | _    |       |  |  |
| Turn-On Rise Time                          | t <sub>R</sub>      | _   | 10.8  | _    |       | $V_{DD} = 20V, V_{GS} = 10V,$                            |  |
| Turn-Off Delay Time                        | tD(OFF)             |     | 44    | _    | ns    | $I_D = 50A, R_g = 2.5\Omega$                             |  |
| Turn-Off Fall Time                         | tF                  |     | 19.5  | _    |       |  |  |
| Reverse Recovery Time                      | trr                 |     | 61.8  | _    | ns    | I- FOA di/dt 1004/vo                                     |  |
| Reverse Recovery Charge                    | Q <sub>RR</sub>     |     | 123   | _    | nC    |  |  |

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

<sup>6.</sup> Thermal resistance from junction to soldering point (on the exposed drain pad).7. Short duration pulse test used to minimize self-heating effect.8. Guaranteed by design. Not subject to product testing.

## DMTH6002LPS





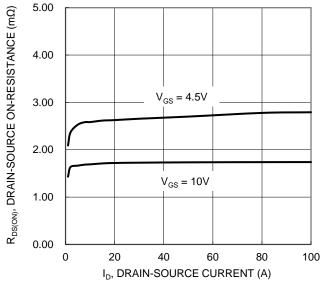


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

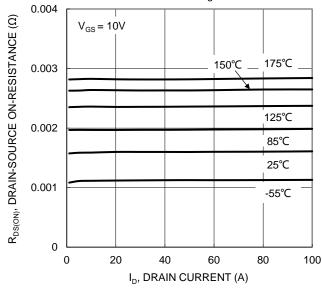
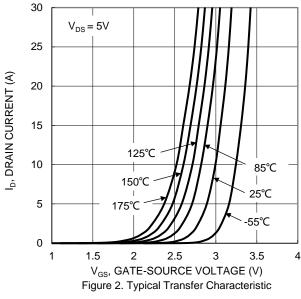
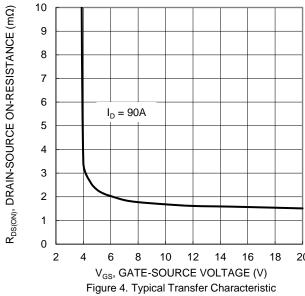


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





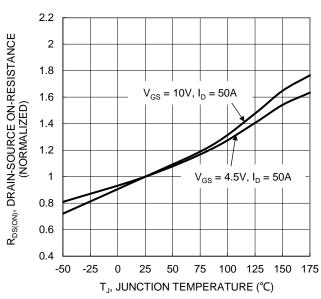


Figure 6. On-Resistance Variation with Temperature





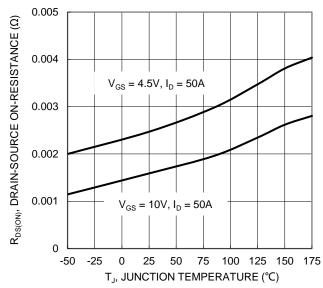
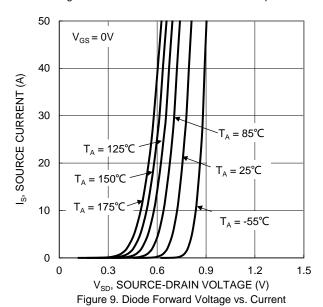


Figure 7. On-Resistance Variation with Temperature



10 8 6  $V_{GS}(V)$ 4  $V_{DS} = 30V, I_{D} = 50A$ 2 0 0 30 120 150 60 90  $Q_{\alpha}$  (nC) Figure 11. Gate Charge

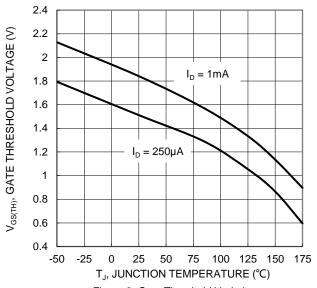
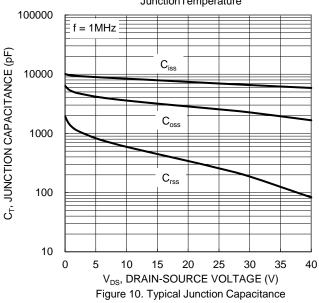


Figure 8. Gate Threshold Variation vs. JunctionTemperature



1000 R<sub>DS(ON)</sub> Limited 100 DRAIN CURRENT (A) 10 =10ms 1 P<sub>W</sub> =100ms T<sub>J(Max)</sub> = 175 °C DC T<sub>C</sub> = 25°C ۵\_ 0.1 Single Pulse DUT on Infinite Heatsink  $V_{GS} = 10V$ 0.01 0.1 10 100 V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



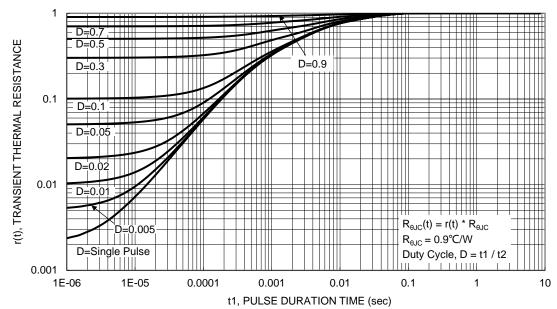


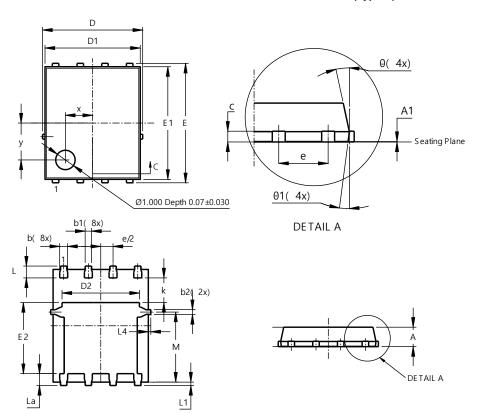
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

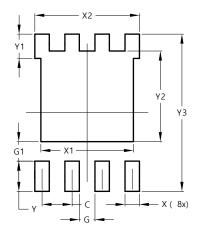
#### PowerDI5060-8 (Type K)



| PowerDI5060-8<br>(Type K) |           |         |       |  |  |
|---------------------------|-----------|---------|-------|--|--|
| Dim                       | Min       | Max     | Тур   |  |  |
| Α                         | 0.90      | 1.10    | 1.00  |  |  |
| A1                        | 0         | 0.05    | 0.02  |  |  |
| b                         | 0.33      | 0.51    | 0.41  |  |  |
| b1                        | 0.300     | 0.366   | 0.333 |  |  |
| b2                        | 0.20      | 0.35    | 0.25  |  |  |
| C                         | 0.23      | 0.33    | 0.277 |  |  |
| D                         | 5         | .15 BS0 | )     |  |  |
| D1                        | 4.85 4.95 |         | 4.90  |  |  |
| D2                        | -         | -       | 3.98  |  |  |
| Е                         | 6         | .15 BS0 | )     |  |  |
| E1                        | 5.75      | 5.85    | 5.80  |  |  |
| E2                        | 3.56      | 3.725   | 3.66  |  |  |
| е                         | 1         | .27BSC  | )     |  |  |
| k                         | -         | -       | 1.27  |  |  |
| L                         | 0.51      | 0.71    | 0.61  |  |  |
| La                        | 0.51      | 0.675   | 0.61  |  |  |
| L1                        | 0.05      | 0.20    | 0.175 |  |  |
| L4                        | -         | -       | 0.125 |  |  |
| М                         | 3.50      | 3.71    | 3.605 |  |  |
| Х                         | -         | -       | 1.400 |  |  |
| y<br>θ                    | -         | -       | 1.900 |  |  |
| θ                         | 10°       | 12°     | 11°   |  |  |
| θ1                        | l 6° 8°   |         |       |  |  |
| All Dimensions in mm      |           |         |       |  |  |

# **Suggested Pad Layout**

#### PowerDI5060-8 (Type K)



| Dimensions | Value<br>(in mm) |  |  |
|------------|------------------|--|--|
| C          | 1.270            |  |  |
| G          | 0.660            |  |  |
| G1         | 0.820            |  |  |
| X          | 0.610            |  |  |
| X1         | 3.910            |  |  |
| X2         | 4.420            |  |  |
| Y          | 1.270            |  |  |
| Y1         | 1.020            |  |  |
| Y2         | 3.810            |  |  |
| Y3         | 6.610            |  |  |



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